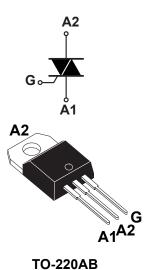


# 16 A 800 V logic level Triac in TO-220AB package



#### **Features**

- Medium current Triac
- · Three quadrants
- ECOPACK2 compliant

### **Applications**

- General purpose AC line load switching
- Motor control circuits
- Small home appliances
- Lighting
- · Inrush current limiting circuits
- Overvoltage crowbar protection

### **Description**

Available in through-hole package, the T1610T-8T Triac can be used for the on/off or phase angle control function in general purpose AC switching.

This device can be directly driven by a microcontroller due to its 10 mA gate current requirement.

| Product status link |  |
|---------------------|--|
| T1610T-8T           |  |

| Product summary                          |       |  |  |  |
|--|-------|--|--|--|
| Order code T1610T-8T                     |       |  |  |  |
| Package TO-220AB                         |       |  |  |  |
| I <sub>T(RMS)</sub> 16 A                 |       |  |  |  |
| V <sub>DRM</sub> /V <sub>RRM</sub>       | 800 V |  |  |  |
| V <sub>DSM</sub> /V <sub>RSM</sub> 900 V |       |  |  |  |
| I <sub>GT</sub>                          | 10 mA |  |  |  |



## 1 Characteristics

Table 1. Absolute maximum ratings (limiting values)

| Symbol                              | Parameter  | Value                 | Unit                    |     |                  |  |
|-------------------------------------|--|-----------------------|-------------------------|-----|------------------|--|
| I <sub>T(RMS)</sub>                 | On-state RMS current (full sine wave)  |                       | T <sub>c</sub> = 129 °C | 16  | Α                |  |
| I <sub>TSM</sub>                    | Non repetitive surge peak on-state current (T <sub>i</sub> initial = 25 °C)  | F = 50 Hz             | t = 20 ms               | 120 | Α                |  |
| TSM                                 | Non repetitive surge peak on-state current (1) initial = 23 (0)  | F = 60 Hz             | t = 16.7 ms             | 126 |                  |  |
| l <sup>2</sup> t                    | $I^2$ t value for fusing, ( $T_j$ initial = 25 °C)   |                       | t <sub>p</sub> = 10 ms  | 95  | A <sup>2</sup> s |  |
| V V                                 | Described and the second secon |                       | T <sub>j</sub> = 150 °C | 600 |                  |  |
| $V_{DRM}, V_{RRM}$                  | Repetitive surge peak off-state voltage  | peak on-state voltage |                         | 800 | V                |  |
| V <sub>DSM</sub> , V <sub>RSM</sub> | Non repetitive surge peak off-state voltage $t_p = 10 \text{ ms}$  |                       |                         |     | V                |  |
| dl/dt                               | Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$ , $tr \le 100 \text{ ns}$  |                       |                         |     | A/µs             |  |
| I <sub>GM</sub>                     | Peak gate current $t_p = 20 \mu s$ $T_j = 150  ^{\circ}C$  |                       |                         |     | Α                |  |
| P <sub>G(AV)</sub>                  | Average gate power dissipation   | 1                     | W                       |     |                  |  |
| T <sub>stg</sub>                    | Storage junction temperature range   | -40 to +150           | °C                      |     |                  |  |
| Тј                                  | Operating junction temperature range   |                       |                         |     | °C               |  |
| T <sub>L</sub>                      | Maximum lead temperature soldering during 10 s   |                       |                         |     | °C               |  |

Table 2. Electrical characteristics ( $T_j = 25$  °C unless otherwise specified)

| Symbol                        | Test condition   | Value                   | Unit     |      |      |
|-------------------------------|--|-------------------------|----------|------|------|
| I <sub>GT</sub>               | $V_D = 12 \text{ V}, R_L = 30 \Omega$  | 1 - 11 - 111            | Min.     | 0.5  | mA   |
| 'GI                           | VD = 12 V, NL = 30 12  | 1 - 11 - 111            | Max.     | 10   | IIIA |
| $V_{GT}$                      | $V_D = 12 \text{ V}, R_L = 30 \Omega$  | 1 - 11 - 111            | Max.     | 1.3  | V    |
| $V_{GD}$                      | $V_D = V_{DRM}$ , $R_L = 3.3 \text{ k}\Omega$ , $T_j = 125 ^{\circ}\text{C}$ | 1 - 11 - 111            | Min.     | 0.2  | V    |
| I <sub>H</sub> <sup>(1)</sup> | I <sub>T</sub> = 500 mA  |                         | Max.     | 15   | mA   |
| IL                            | I <sub>G</sub> = 1.2 x I <sub>GT</sub>                                       | 1 - 111                 | Max.     | 20   | mA   |
| 'L                            |  | II                      | IVIAX.   | 25   |      |
| dV/dt <sup>(1)</sup>          | $V_D = V_R = 536 \text{ V}$ , gate open                                      | T <sub>j</sub> = 125 °C | Min.     | 250  | Muo  |
| uv/ut <sup>(*)</sup>          | V <sub>D</sub> = V <sub>R</sub> = 402 V, gate open                           | T <sub>j</sub> = 150 °C | IVIII I. | 170  | V/µs |
|                               | (4)//41/2 = 0.4.1//  | T <sub>j</sub> = 125 °C |          | 21.6 | A/ms |
| 4 H 4 H 5 (1)                 | $(dV/dt)c = 0.1 V/\mu s$   | T <sub>j</sub> = 150 °C | Min.     | 15.1 |      |
| (dl/dt)c <sup>(1)</sup>       | (4)/(4) - 40 )/(   | T <sub>j</sub> = 125 °C | IVIIII.  | 11.3 |      |
|                               | (dV/dt)c = 10 V/μs   | T <sub>j</sub> = 150 °C |          | 5    |      |

<sup>1.</sup> For both polarities of A2 referenced to A1

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**Table 3. Static characteristics** 

| Symbol                         | Test                                    | Test conditions         |      |           | Unit |
|--------------------------------|---|-------------------------|------|-----------|------|
| V <sub>T</sub> <sup>(1)</sup>  | $I_{TM}$ = 22.6 A, $t_p$ = 380 $\mu$ s  | T <sub>j</sub> = 25 °C  | Max. | 1.55      | V    |
| V <sub>TO</sub> <sup>(1)</sup> | Threshold voltage                       | T <sub>j</sub> = 150 °C | Max. | Max. 0.85 |      |
| R <sub>d</sub> <sup>(1)</sup>  | Dynamic resistance                      | T <sub>j</sub> = 150 °C | Max. | 27        | mΩ   |
|                                | V <sub>D</sub> = V <sub>R</sub> = 800 V | T <sub>j</sub> = 25 °C  | May  | 7.5       | μA   |
| $I_{DRM}$ , $I_{RRM}$          | v <sub>D</sub> - v <sub>R</sub> - 000 v | T <sub>j</sub> = 125 °C | Max. | 1.0       | mΛ   |
|                                | V <sub>D</sub> = V <sub>R</sub> = 600 V | T <sub>j</sub> = 150 °C | Max. | 3.0       | mA   |

<sup>1.</sup> For both polarities of A2 referenced to A1

**Table 4. Thermal parameters** 

| Symbol               | Parameter             | Value | Unit |
|----------------------|-----------------------|-------|------|
| R <sub>th(j-c)</sub> | Junction to case (AC) | 1.1   | °C/W |
| R <sub>th(j-a)</sub> | Junction to ambient   | 60    | °C/W |



### 1.1 Characteristics (curves)

Figure 1. Maximum power dissipation versus on-state RMS current

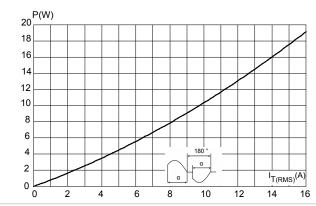


Figure 2. On-state RMS current versus case temperature  $I_{T(RMS)}\!(A)$ 16 14 12 10 8 6 2 T<sub>c</sub>(°C) 0 75 50 100 150 0 25 125

Figure 3. On-state RMS current versus ambient temperature (free air convection)

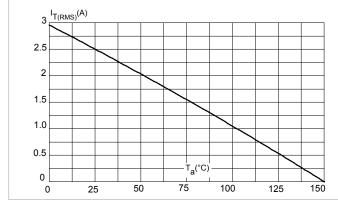


Figure 4. Relative variation of thermal impedance versus pulse duration

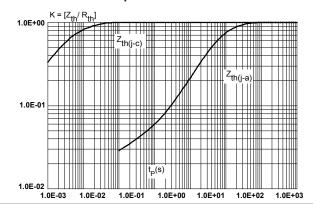


Figure 5. Relative variation of gate trigger voltage and current versus junction temperature (typical values)

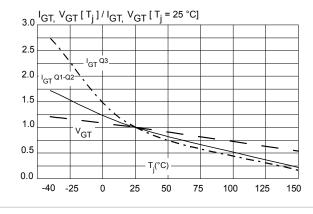
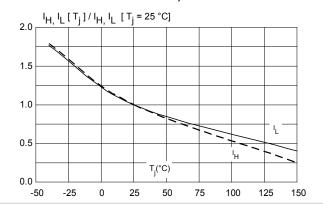


Figure 6. Relative variation of holding current and latching current versus junction temperature (typical values)



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Figure 7. Surge peak on-state current versus number of cycles

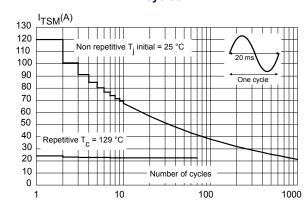


Figure 8. Non repetitive surge peak on-state current

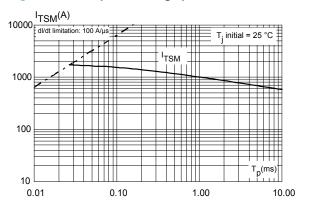


Figure 9. On-state characteristics (maximum values)

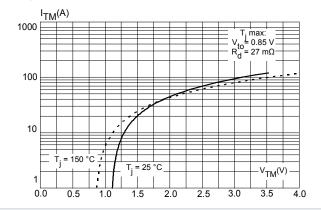


Figure 10. Relative variation of critical rate of decrease of main current versus junction temperature (typical values)

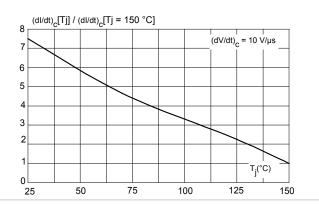


Figure 11. Relative variation of static dV/dt immunity versus junction temperature (typical values)

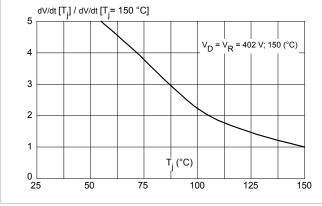
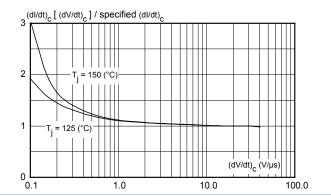


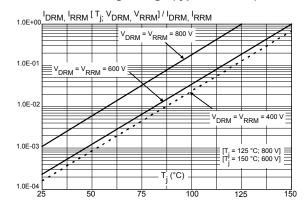
Figure 12. Relative variation of critical rate of decrease (di/dt)c of main current versus reapplied (dV/dt)c (maximum values)



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Figure 13. Relative variation of leakage current versus junction temperature for different values of blocking voltage (typical values)



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### 2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

#### 2.1 TO-220AB package information

• Epoxy resin is halogen free and meets UL94 flammability standard, level V0

В

- Lead-free plating package leads
- Recommended torque: 0.4 to 0.6 N·m

Resin gate 0.5 mm max. protusion<sup>(1)</sup>

A

14

13

12

22

b1

Resin gate 0.5 mm max. protusion<sup>(1)</sup>

Μ

с1

Figure 14. TO-220AB package outline

(1)Resin gate position accepted in one of the two positions or in the symmetrical opposites.

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Table 5. TO-220AB package mechanical data

|      |       |             | D     | imensions |        |        |
|------|-------|-------------|-------|-----------|--------|--------|
| Ref. |       | Millimeters |       |           | Inches |        |
|      | Min.  | Тур.        | Max.  | Min.      | Тур.   | Max.   |
| Α    | 15.20 |             | 15.90 | 0.5984    |        | 0.6260 |
| a1   |       | 3.75        |       |           | 0.1476 |        |
| a2   | 13.00 |             | 14.00 | 0.5118    |        | 0.5512 |
| В    | 10.00 |             | 10.40 | 0.3937    |        | 0.4094 |
| b1   | 0.61  |             | 0.88  | 0.0240    |        | 0.0346 |
| b2   | 1.23  |             | 1.32  | 0.0484    |        | 0.0520 |
| С    | 4.40  |             | 4.60  | 0.1732    |        | 0.1811 |
| c1   | 0.49  |             | 0.70  | 0.0193    |        | 0.0276 |
| c2   | 2.40  |             | 2.72  | 0.0945    |        | 0.1071 |
| е    | 2.40  |             | 2.70  | 0.0945    |        | 0.1063 |
| F    | 6.20  |             | 6.60  | 0.2441    |        | 0.2598 |
| 1    | 3.73  |             | 3.88  | 0.1469    |        | 0.1528 |
| L    | 2.65  |             | 2.95  | 0.1043    |        | 0.1161 |
| 12   | 1.14  |             | 1.70  | 0.0449    |        | 0.0669 |
| 13   | 1.14  |             | 1.70  | 0.0449    |        | 0.0669 |
| 14   | 15.80 | 16.40       | 16.80 | 0.6220    | 0.6457 | 0.6614 |
| М    |       | 2.6         |       |           | 0.1024 |        |

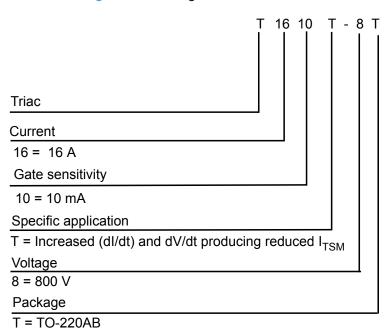
<sup>1.</sup> Inch dimensions are for reference only.

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# 3 Ordering information

Figure 15. Ordering information scheme



**Table 6. Ordering information** 

| Order code | Marking   | Package  | Weight | Base qty. | Delivery mode |
|------------|-----------|----------|--------|-----------|---------------|
| T1610T-8T  | T1610T-8T | TO-220AB | 2.0 g  | 50        | Tube          |

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## **Revision history**

Table 7. Document revision history

| Date        | Version | Changes                        |
|-------------|---------|--------------------------------|
| 23-Oct-2014 | 1       | Initial release.               |
| 17-Sep-2019 | 2       | Updated Figure 14 and Table 5. |
| 23-Sep-2019 | 3       | Updated Table 2.               |



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